



30V N-Channel Trench Power MOSFET

General Description

The SJG30ND262 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a wide variety of applications.

Features

- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(ON_TYP)}$	22.5	m Ω
I_D	5	A
Q_G	7	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJG30ND262	SJG30ND262	SOT23-6L	Tape	\	\	3000 Pcs

Table 1. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 12	V
I_D	Drain Current-Continuous($T_A=25^\circ\text{C}$)	5	A
	Drain Current-Continuous($T_A=100^\circ\text{C}$)	3.1	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	20	A
P_D	Maximum Power Dissipation($T_A=25^\circ\text{C}$)	1.1	W
	Maximum Power Dissipation($T_A=100^\circ\text{C}$)	0.4	W
E_{AS}	Avalanche energy (Note 2)	20	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		110	$^\circ\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =30V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5		1.5	V
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =1.5A		7.3		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =1.5A T _J =25℃		22.5	28	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =1A T _J =25℃		24.5	32.6	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =2.5V, I _D =1A T _J =25℃		31.8	42.3	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V,V _{GS} =0V, f=100KHz		488		pF
C _{oss}	Output Capacitance			44		pF
C _{rss}	Reverse Transfer Capacitance			35		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=100KHz		5.4		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =10Ω, R _{GEN} =3Ω		5		nS
t _r	Turn-on Rise Time			12		nS
t _{d(off)}	Turn-Off Delay Time			24		nS
t _f	Turn-Off Fall Time			2		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =1.5A		7		nC
Q _{gs}	Gate-Source Charge			1.6		nC
Q _{gd}	Gate-Drain Charge			1.6		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				5	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =1.5A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =1.5A, dI/dt=500A/μs		8.5		ns
Q _{rr}	Reverse Recovery Charge	I _F =1.5A, dI/dt=500A/μs		3.4		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

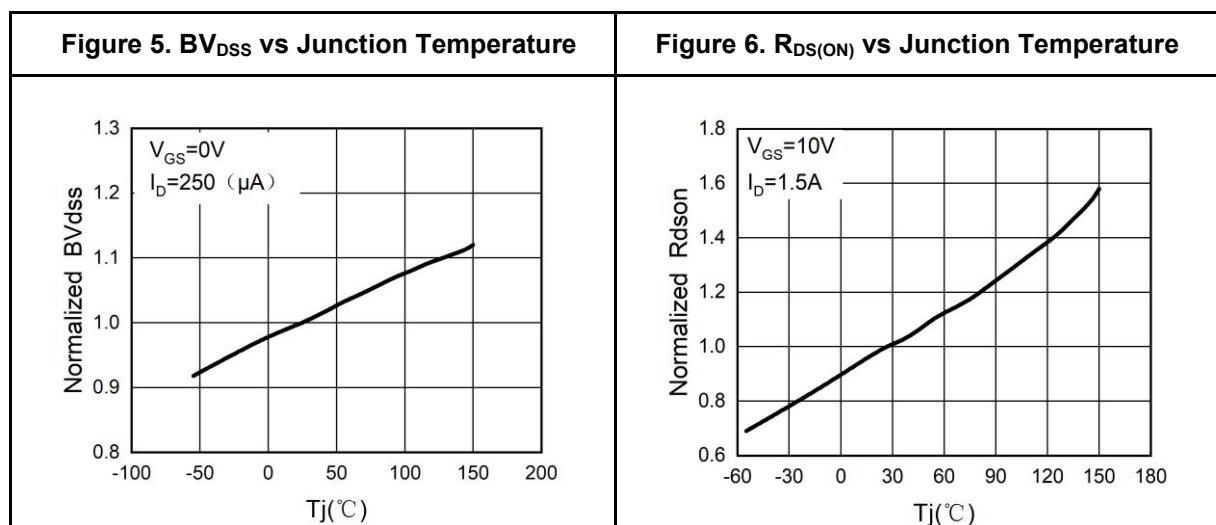
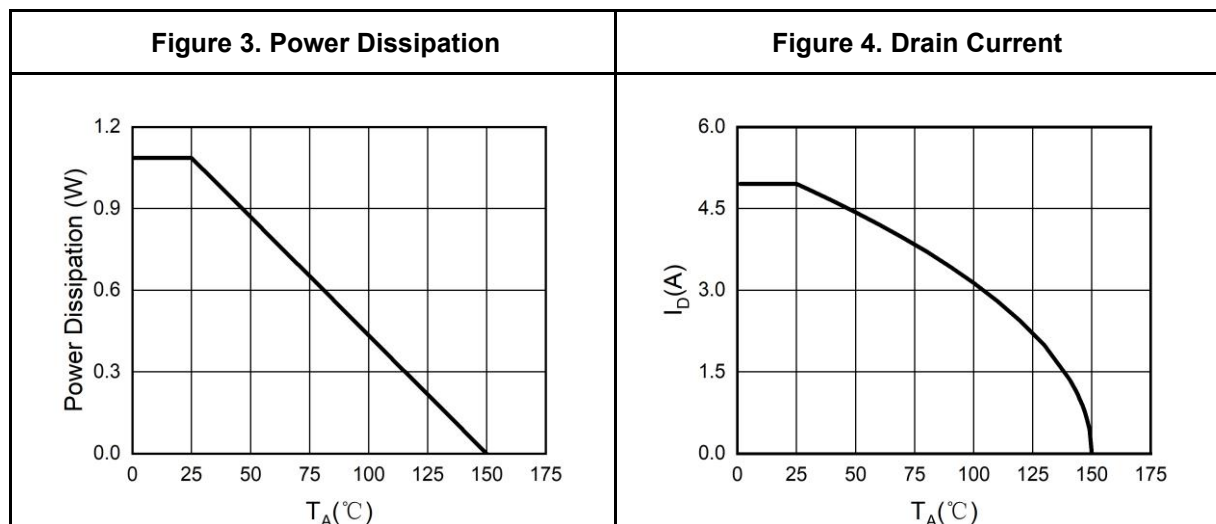
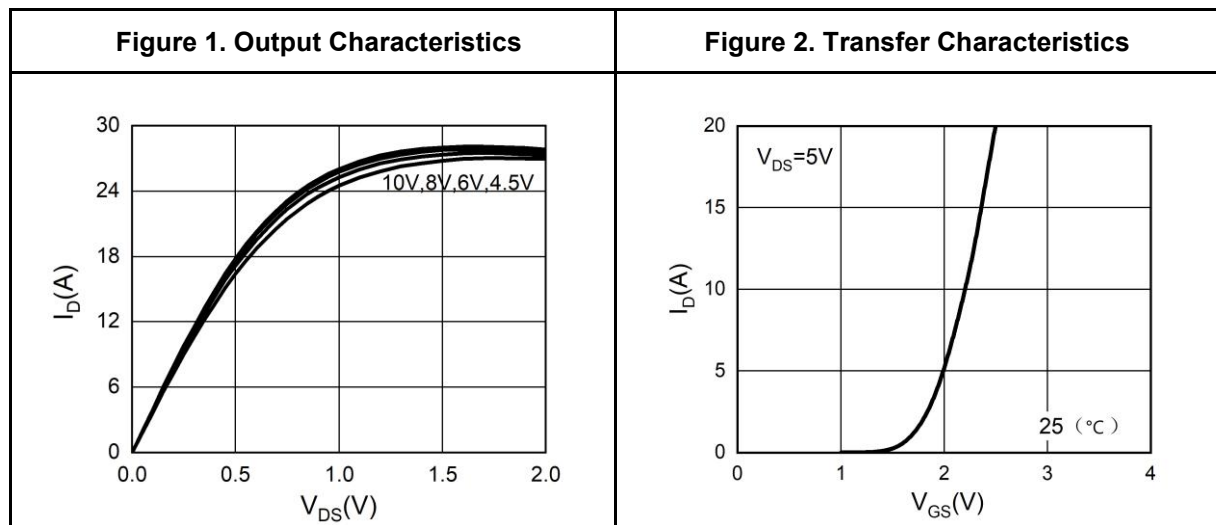
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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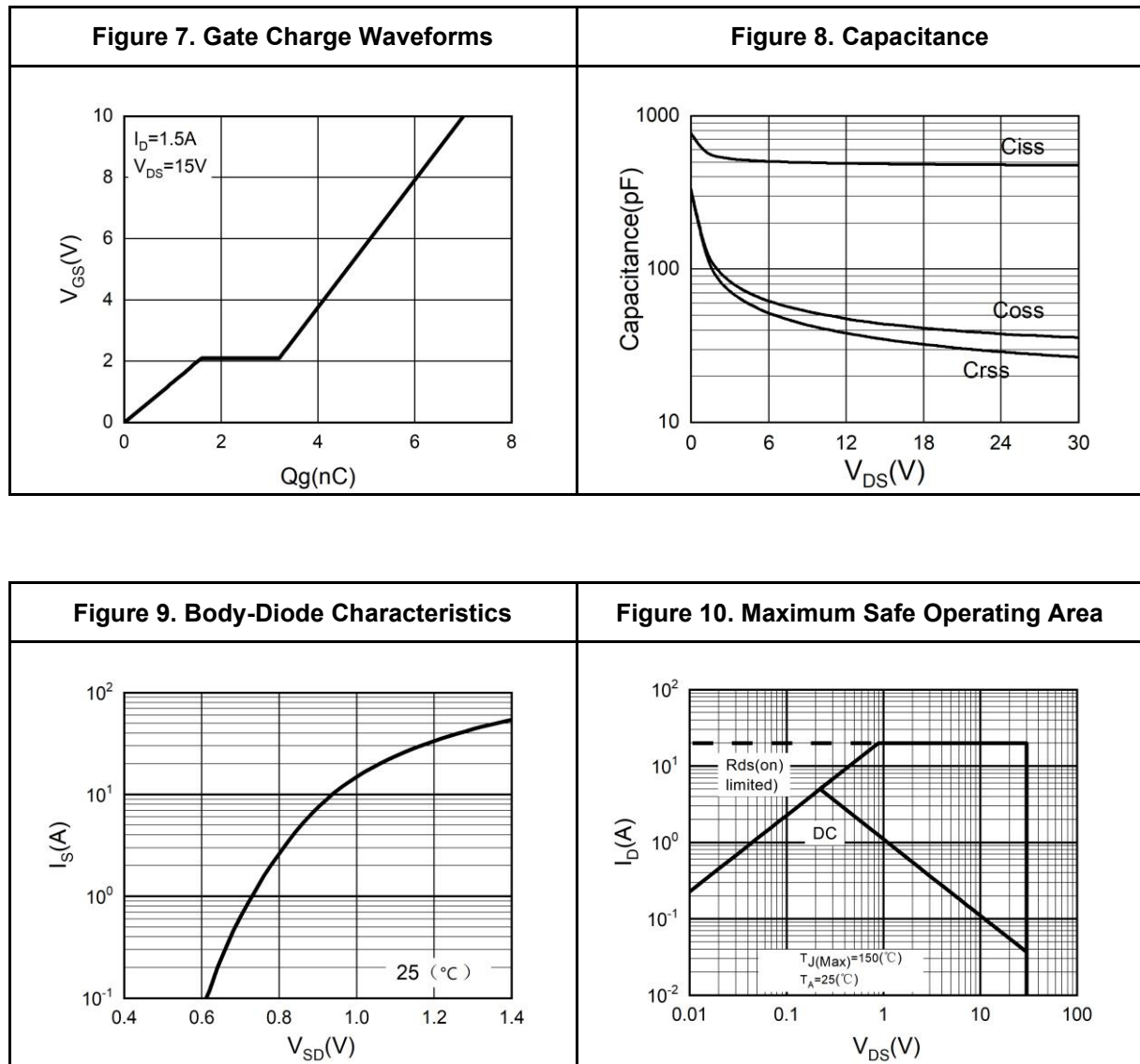
Typical Electrical And Thermal Characteristics (Curves)





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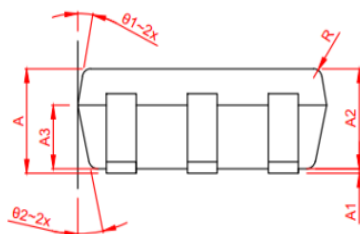
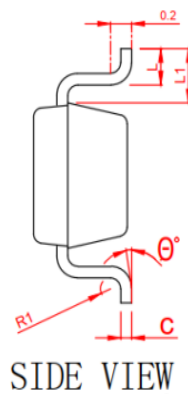
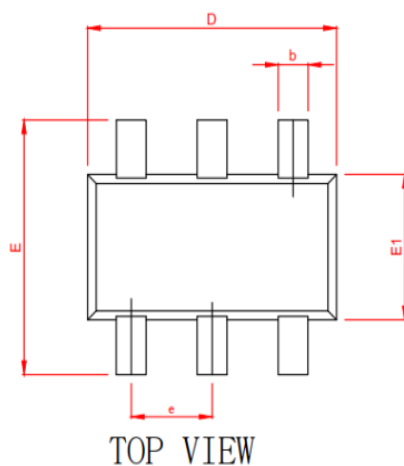
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SOT-23-6L Package Information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.06	1.15	1.24
* A1	0.01	0.05	0.09
* A2	1.05	1.10	1.15
A3	0.65	0.70	0.75
* b	0.30	0.35	0.45
* c	0.127REF		
* D	2.87	2.92	2.97
* E	2.72	2.80	2.88
* E1	1.55	1.60	1.65
* e	0.95BSC		
* L	0.32	0.40	0.48
* L1	0.55	0.60	0.65
R	0.10 REF		
R1	0.12 REF		
* θ	0	--	8°
θ1	8°	10°	12°
θ2	10°	12°	14°



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